

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory		User Part Number BAS16LD Part Description												
										Nexperia DHAM	Small Signal E	Bipolar Diode		
								Assembly reliability labs		MCD package				
Based on AEC-Q101 Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects								
	TEST													
	Pre- and Post-Stress													
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below								
		JESD22-A113												
		Bake Tamb = 125 °C	24 hours											
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours											
# A1	Preconditioning	Reflow soldering	3 cycles	113	9040	0								
		MIL-STD-750-1												
	HTRB	M1038 Method A												
	High Temperature Reverse	Tj = Tjmax, Vr = 100% of max. datasheet												
# B1	Bias	reverse voltage	1000 hours	67	5360	0								
	TC	JESD22-A104												
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	28	2240	0								
		JESD22-A102												
	AC	Tamb = 121 °C, RH = 100 %												
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	28	2240	0								
		JECD22 A101												
	H3TRB	JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of												
" AO II	High Humidity High Temperature Reverse Bias		10001	20	22.40	•								
# A2 alt	Temperature Reverse Bias		1000 hours	28	2240	0								
		MIL-STD-750 Method 1037												
	IOL	ton = toff, devices powered to insure ΔTj =				_								
# A5	Intermittent Operating Life	100 °C for 15000 cycles	1000 hours	29	2320	0								
	RSH	JESD22-A111												
# C8	Resistance to Solder Heat		10 s	2 2	n n	n 2								
# 6	SD	200 0 = 3 0	10.5	n.a.	n.a.	n.a.								
# C10	Solderability	J-STD-002		63	630	0								
# C10	30idel ability	J-31D-002		63	630	0								

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia					
DHAM	Small Signal Bipolar Diode	5360	0	0.79	1.26E+09

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